

# Trends in III-V and II-VI Compounds

➔ Larger atoms, weaker bonds, smaller  $U$ , smaller  $E_g$ , higher  $\mu$ , more costly!

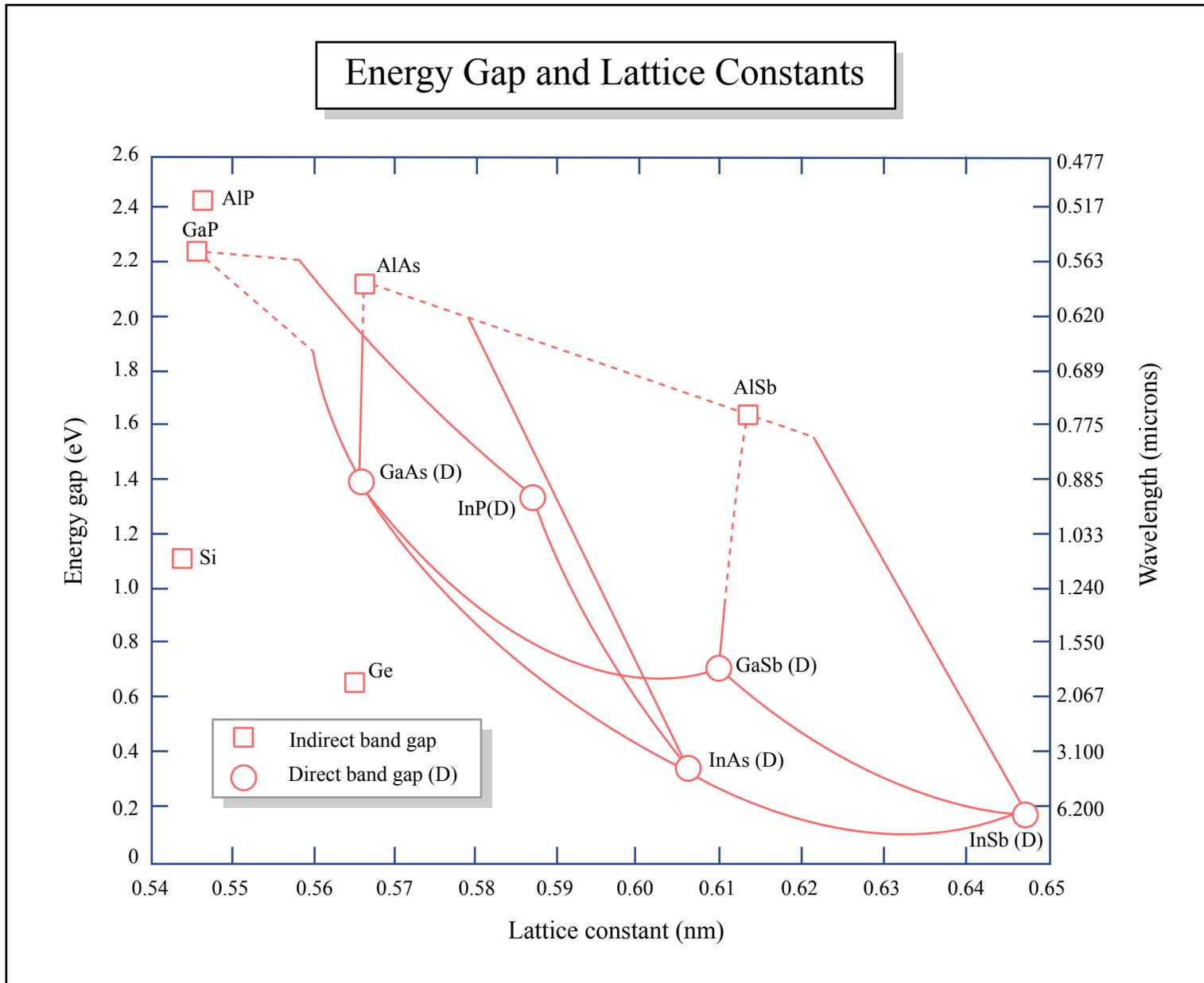
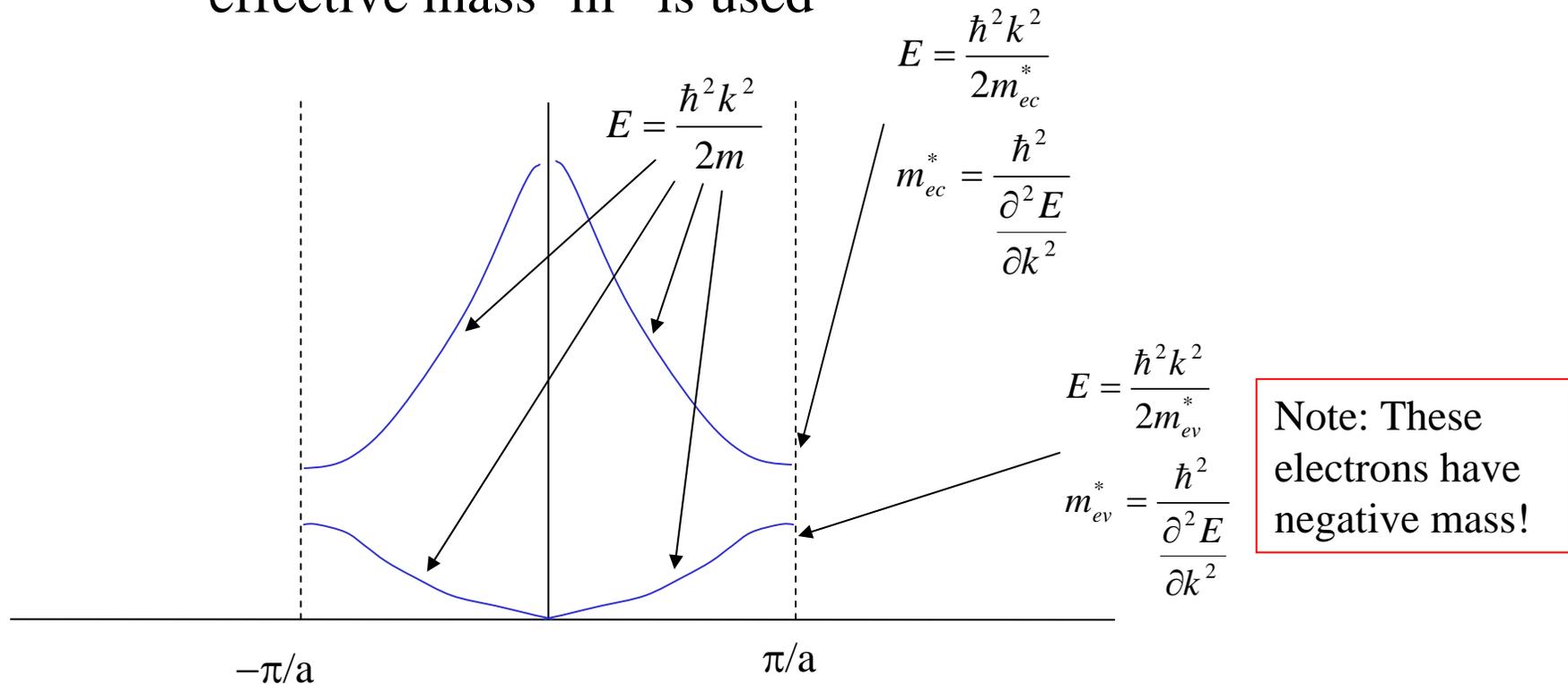


Figure by MIT OpenCourseWare.

# Properties of non-free e-

- Electrons near the diffraction condition are not approximated as free
- Their properties can still be viewed as free e- if an 'effective mass'  $m^*$  is used

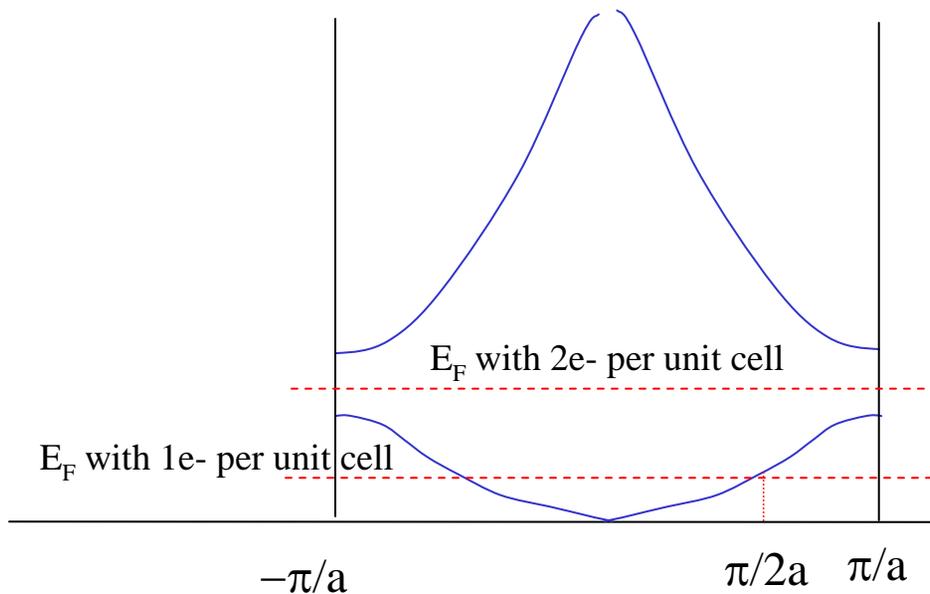


# 1-D Crystal Metals and Insulators

- How do band gaps affect properties of materials?
- Only electrons near  $E_F$  participate in properties
- If  $E_F$  is in the middle of the band, free e- and metallic behavior
- If  $E_F$  is near the band gap, changes in materials properties may occur
- Need to find out where  $E_F$  is!

$$N = \frac{2k_F L}{\pi} = \frac{2L}{a}$$

Where  $k_F = \pi/a$  if we want to see how many electrons are in first band



Note:  $L/a$  is the number of unit cells in the 1-D crystal; therefore, the number of electrons per unit cell, which depends on  $n$  and the crystal structure, determine where  $E_F$  is with respect to the band gap

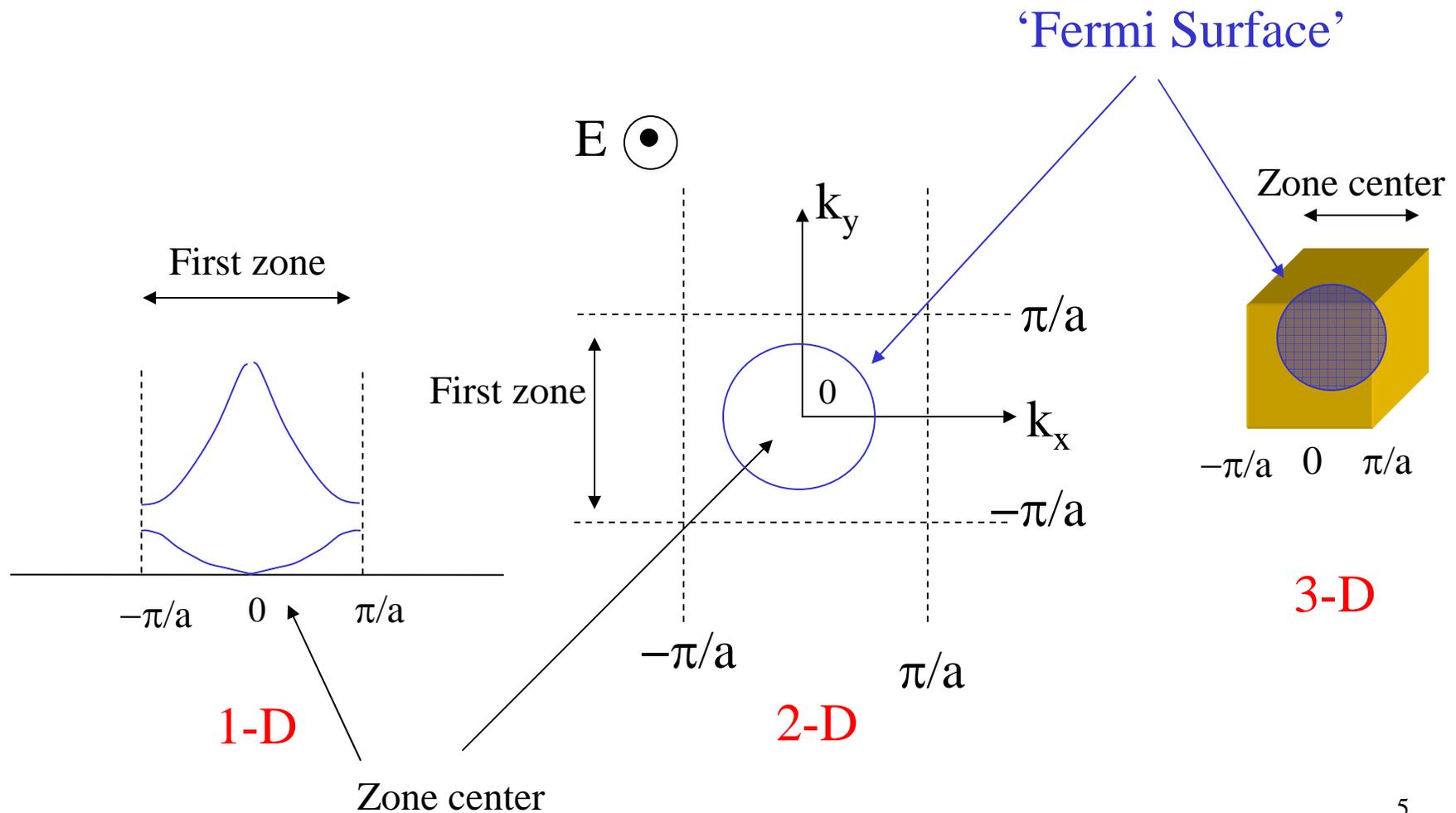
# 1-D Crystal Metals and Insulators

- 2e- per unit cell:  $E_F$  at band edge: 2 possibilities
  - Band gap  $\gg kT$ : electrons at band max can not accept energy from electric fields; no conduction, *insulating behavior*
  - Band gap near  $kT$ : some thermal fluctuations large enough to allow population of second band; carriers are there, but less than for free e-, *semimetal*
- 1e- per unit cell:  $E_F$  in middle of band: free e-, *metallic*

Note: crystal structure (number of atoms per primitive cell) and valence (number of conduction electrons per atom), combined with band gap size, determine the electronic properties

# Higher Dimensions (2 and 3-D)

- 1-D:  $E(k_x)$ ; 2-D:  $E(k_x, k_y)$ ; 3-D:  $E(k_x, k_y, k_z)$



# Metals and Insulators

- Covalent bonds, weak  $U$  seen by  $e^-$ , with  $E_F$  being in mid-band area: free  $e^-$ , *metallic*
- Covalent or slightly ionic bonds, weak  $U$  to medium  $U$ , with  $E_F$  near band edge
  - $E_F$  in or near  $kT$  of band edge: *semimetal*
  - $E_F$  in gap: *semiconductor*
- More ionic bonds, large  $U$ ,  $E_F$  in very large gap, *insulator*

# Insulators

- Very large band gaps=no conduction electrons at reasonable temperatures
- All electrons are bound
- Optical properties of insulators are derived from the electric field being able to temporarily move electrons: **polarization**
- We will return to the interaction of E-field with bound electrons in Dielectrics Section